Substitute for Form 1449) A & R/PTO	.		Complete if Known		
	, 4.	1		Application Number	10/689,024	
INFOR	RMATION	DISCLOS	SURE	Confirmation Number	4493	
STATI	EMENT B	Y APPLIC	CANT	Filing Date	October 21, 2003	
				First Named Inventor	Takashi UDAGAWA	
(use	as many shee	ts as nėcessa	ry)	Art Unit	2826	
				Examiner Name	Minh Loan Tran	
Sheet	1	of	1	Attorney Docket Number	Q72568	

			U.S.	PATENT DOCU	MENTS
Examiner Cite Initials* No.	Cite	Document N	umber	Publication Date	
	Number Kind Code ¹ (if known)		MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	
MLT		US 6,069,021	B	05-30-2000	TERASHIMA et al.
		US O	El		
		US	5/		/
		US MAN 2	7 2005		
		103 1.	4. 41	/	
		US E		/	
		US 🐎	ale;		
		US US	EATT		
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Cite Initials No. 1	Foreign Patent Document			Publication Date	Name of Patentee or		
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶
MLT		JР	10-56202		02-24-1998	SHOWA DENKO KK	Abstract
MLT		JР	55-3834		01-26-1980		Abstract
MLT		JР	10-107315		04-24-1998	SHOWA DENKO KK	Abstract
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						:	
					/		

		NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	the state of the s					
Isamu AKASAKI (compiler), "Advanced Electronics Series, I-21, Group-III Nitride Semiconductor", 1 st edition, pp. 288-289, Baifukan (December 8, 1999) Isamu AKASAKI et al.; "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga _{1-x} Al _x N (0 <x≤0.4) (1989)<="" (the="" 209-219="" 98,="" by="" crystal="" films="" grown="" growth="" journal="" movpe";="" netherlands);="" of="" on="" pp.="" sapphire="" substrate="" td="" vol.=""></x≤0.4)>						
					MLT	Isamu AKASAKI (compiler); "Advanced Electronics Series, I-21, Group-III Nitride Semiconductor"; 1 st edition, pp. 211-213, Baifukan (December 8, 1999)
i						

Examiner Signature	Minhloan	Tran	Date Considered	8 105

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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